







TPS38700S-Q1 JAJSQQ7 - JULY 2023

# TPS38700S-Q1 最大 6 チャネル、6 GPO、SYNC に対応する I<sup>2</sup>C を備えた電源シ ーケンサ

# 1 特長

- 下記内容で AEC-Q100 認定済み:
  - デバイス温度グレード 1:-40℃~+125℃
- 最新 SoC 向けシーケンシング
  - 最大 6 つの電源レールのシーケンシングが可能
  - パワーアップ / パワーダウン・タイミング・シーケンス を I2C 経由でプログラム可能
    - 125µs~64ms (125µs 刻み)
    - 500µs~25ms (500µs 刻み)
- システムの堅牢性
  - 動作エラー中にシステムを安全状態にラッチするア クティブ Low オープン・ドレイン NIRQ
  - 同期ピンを搭載した TPS389006-Q1 などのマル チチャネル・スーパーバイザと接続し、完全な電圧 監視とシーケンシング状況を実現
  - バッテリ・バックアップ機能によるパワーアウト時の 診断エラー報告
  - 高温環境でのデバイスのサーマル・シャットダウン

# 2 アプリケーション

- 先進運転支援システム (ADAS)
- 車載用カメラ・モジュール
- FPGA 電源シーケンシング
- マイクロプロセッサおよびマイクロコントローラのシーケ ンシング
- 複数電源シーケンシング

#### 3 概要

TPS38700S-Q1 デバイスは、ウィンドウ・ウォッチドッグを 備え I<sup>2</sup>C でプログラム可能な統合型マルチチャネル電圧 シーケンサです。本デバイスは、24 ピンの 4mm × 4mm VQFN パッケージで供給されます。

このマルチチャネル電圧シーケンサは、精密なパワーアッ プ / パワーダウン・シーケンス動作を必要とするシステムに 最適であり、マルチチャネル電圧スーパーバイザと接続で きます。デフォルトで、このデバイスは事前プログラム済み の OTP オプションを利用できますが、必要に応じて、I<sup>2</sup>C を使用して、パワーアップ / パワーダウン・シーケンス、ウォ ッチドッグの設定、シーケンス・タイミングの各オプションを 再プログラムすることもできます。

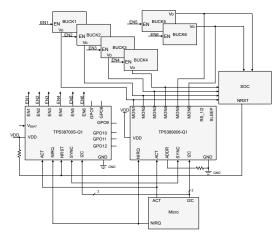
フレキシブルかつプログラマブルな電圧レール・シーケン ス機能、低い静止電流、小さいフットプリントにより、このデ バイスはほとんどのアプリケーションの要件を満たすことが できます。

TPS38700S-Q1 で SYNC を使用すると、システムのパワ ーアップ方法をより詳細に制御できます。これを実現する には、TPS38700S-Q1 は SYNC 信号を使用して、電流 レールが許容可能なレベルまでパワーアップしたときにの み次のイネーブル信号を起動します。 さらに、 TPS38700S-Q1 ではカスタム遅延オプションも使用でき ます。TPS38700S-Q1 は、TPS389006-Q1 と組み合わ せて使用するように設計されています。

#### 製品情報

部品番号	パッケージ <sup>(1)</sup>	本体サイズ (公称)
TPS38700S-Q1	VQFN (24)	4mm × 4mm

利用可能なすべてのパッケージについては、データシートの末尾 にある注文情報を参照してください。



マルチチャネル電圧シーケンサおよびモニタ

English Data Sheet: SNVSCG1



# **Table of Contents**

1 特長1	8.3 Feature Description	14
<b>2</b> アプリケーション1	8.4 Register Map Table	
3 概要1	9 Application and Implementation	.36
4 Revision History3	9.1 Application Information	. 36
5 Device Comparison4	9.2 Typical Application	. 37
6 Pin Configuration and Functions5	10 Power Supply Recommendations	42
7 Specifications	10.1 Power Supply Guidelines	42
7.1 Absolute Maximum Ratings7	11 Layout	43
7.2 ESD Ratings7	11.1 Layout Guidelines	. 43
7.3 Recommended Operating Conditions7	11.2 Layout Example	. 43
7.4 Thermal Information8	12 Device and Documentation Support	44
7.5 Electrical Characteristics8	12.1 Device Nomenclature	44
7.6 Timing Requirements9	12.2 Receiving Notification of Documentation Updates.	. 44
7.7 Typical Characteristics11	12.3 サポート・リソース	. 44
8 Detailed Description12	12.4 Trademarks	. 44
8.1 Overview12	12.5 静電気放電に関する注意事項	. 44
8.2 Functional Block Diagram13	12.6 用語集	. 44

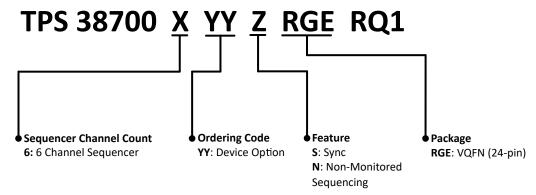
# **4 Revision History**

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

DATE	REVISION	NOTES
July 2023	*	Initial Release

# **5 Device Comparison**

図 5-1 shows the device nomenclature of the TPS38700S-Q1 device. See 表 12-1 for more information regarding device ordering codes. Contact TI sales representatives or on TI's E2E forum for details and availability of other options; minimum order quantities apply.



Refer 'Mechanical, Packaging and Orderable Information' section on for list of released orderable. For any other orderable, contact local TI support.

図 5-1. TPS38700S-Q1 Device Nomenclature

# **6 Pin Configuration and Functions**

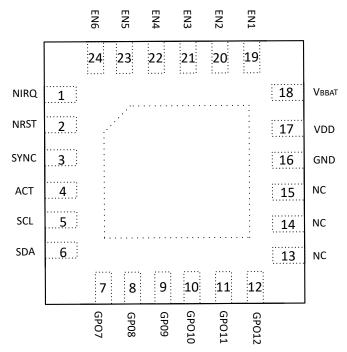


図 6-1. RGE Package 24-Pin VQFN TPS38700 Top View



## 表 6-1. Pin Functions

	PIN		
NO. TPS38700S-Q1		1/0	DESCRIPTION
NO.	NAME		
1	NIRQ	0	Interrupt Pin (open-drain, active-low)
2	NRST	0	Reset Pin (open-drain, active-low)
	0,410		Active low input needed for enabling and disabling voltage rails during the Power Up
3	SYNC	I	and Power Down sequences. For more information check out セクション 8.1 and セクション 8.3.2.
4	ACT	I	ACT pin (logic high starts power up sequence, logic low starts power down sequence)
5	SCL	I	I2C clock pin
6	SDA	I / O I2C data pin	
7	GPO7	0	GPO7 (open-drain)
8	GPO8	0	GPO8 (open-drain)
9	GPO9	0	GPO9 (open-drain)
10	GPO10	0	GPO10 (open-drain)
11	GPO11	0	GPO11 (open-drain)
12	GPO12	0	GPO12 (open-drain)
13	NC	NA	Leave pin open circuit. Do not connect to anything.
14	NC	NA	Leave pin open circuit. Do not connect to anything.
15	NC	NA	Leave pin open circuit. Do not connect to anything.
16	GND	-	Ground
17	VDD	-	Power supply
18	V <sub>BBAT</sub>	-	Backup battery supply. For more information on the backup state check out セクション 8.3.4.
19	EN1	0	Enable 1 (open-drain)
20	EN2	0	Enable 2 (open-drain)
21	EN3	0	Enable 3 (open-drain)
22	EN4	0	Enable 4 (open-drain)
23	EN5	0	Enable 5 (open-drain)
24	EN6	0	Enable 6 (open-drain)

# 7 Specifications

# 7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
Voltage	VDD, V <sub>BBAT</sub>	-0.3	6	V
Voltage	GPOx	-0.3	6	V
Voltage	SCL, SDA (OTP=3.3V)	-0.3	5.5	V
	Continuous total power dissipation	See the Thermal Information		
Temperature <sup>(2)</sup>	Operating junction temperature, T <sub>J</sub>	-40	150	°C
Temperature (=)	Operating free-air temperature, T <sub>A</sub>	-40	125	°C
	Storage temperature, T <sub>stg</sub>	-65	150	°C

<sup>(1)</sup> Stresses beyond values listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) As a result of the low dissipated power in this device, it is assumed that  $T_J = T_A$ .

# 7.2 ESD Ratings

				VALUE	UNIT
		Human-body model (HBM), per ANSI/ESDA/JEDE	C JS-001 <sup>(1)</sup>	±2000	
V <sub>(ESD)</sub>	Electrostatic discharge	Charged-device model (CDM), per AEC	All pins	±500	V
		Q100-011	Corner pins	±750	

(1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification

## 7.3 Recommended Operating Conditions

		MIN	NOM MAX	UNIT
VDD	Supply pin voltage	2.2	5.5	V
V <sub>BBAT</sub>	Battery back up	1.8	5.5	V
I <sub>NRST,</sub> I <sub>NIRQ,</sub> I <sub>E</sub>	Pin Currents	0	±1	mA
GPOx	Pin voltage	0	5.5	V
SCL, SDA	Pin Voltage (OTP=3.3V)	0	4	V
R <sub>UP</sub>	Pull-up resistor (Open Drain configuration)	10	100	kΩ
TJ	Junction temperature (free-air temperature)	-40	125	°C



## 7.4 Thermal Information

		TPS38700x-Q1	
	THERMAL METRIC(1)	RGE (VQFN)	UNIT
		PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	53.4	°C/W
R <sub>0JC(top)</sub>	Junction-to-case (top) thermal resistance	51.4	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	17.2	°C/W
$\Psi_{JT}$	Junction-to-top characterization parameter	0.3	°C/W
$\Psi_{JB}$	Junction-to-board characterization parameter	20.7	°C/W
R <sub>0JC(bot)</sub>	Junction-to-case (bottom) thermal resistance	3.9	°C/W

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

## 7.5 Electrical Characteristics

At 2.2 V  $\leq$  VDD  $\leq$  5.5 V, NRST/NIRQ Voltage = 10 k $\Omega$  to VDD, NRST/NIRQ load = 10 pF, and over the operating free-air temperature range of – 40°C to 125°C, unless otherwise noted. Typical values are at T<sub>A</sub> = 25°C, typical conditions at VDD= 3.3 V.

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Common Par	ameters					
VDD	Input supply voltage		2.2		5.5	V
V <sub>BBAT</sub>	Backup battery voltage range		1.85		5.5	V
UVLO_VDDR	UVLO VDD	Rising threshold			2.2	V
UVLO_VDDF	UVLO VDD	Falling threshold/switch over to V <sub>BBAT</sub>	1.90		2	V
UVLO_V <sub>BBAT</sub>	UVLO Battery backup	Falling threshold			1.85	V
POR	Power ON reset voltage, all outputs guaranteed to be stable above this value	Falling threshold			1.39	V
I <sub>DD</sub>	Supply current into VDD pin ACT=High	VDD ≤ 5.5 V, power up sequence complete		45	75	μΑ
I <sub>DD</sub>	Supply current into VDD pin ACT=Low	VDD ≤ 5.5 V ,power down sequence complete		35	60	μΑ
I <sub>BBAT</sub>	Supply current from V <sub>BBAT</sub>	V <sub>BBAT</sub> ≤ 5.5 V		35	60	μA
I <sub>LKG_NRST</sub>	Output leakage current (NRST)	VDD=V <sub>NRST</sub> = 5.5 V			300	nA
I <sub>LKG_NIRQ</sub>	Output leakage current (NIRQ)	VDD=V <sub>NIRQ</sub> = 5.5 V			300	nA
ACT_L	Logic Low input				0.36	V
ACT_H	Logic high input		0.84		VDD - 0.2	V
SYNC_H	Input High	Io = 1mA	1.1			V
SYNC_L	Input Low	Io = 1mA			0.36	V
ACT	Internal Pull down			100		kΩ
NRST	Output Low	Open-Drain (10 kΩ pull up)			0.1	V
NIRQ	Output Low	Open-Drain (10 kΩ pull up)			0.1	V
ENx	Output Low	Open-Drain (10 kΩ pull up)			0.1	V
GPOx	Output Low	Open-Drain (10 kΩ pull up)			0.1	V
OSC	Internal oscillator tolerance		-5		5	%
I <sub>lkg(BBAT)</sub>	Leakge current from V <sub>BBAT</sub>	V <sub>BBAT</sub> > 1.85V			300	nA
TSD	Thermal Shutdown			165		°C

## 7.5 Electrical Characteristics (continued)

At 2.2 V  $\leq$  VDD  $\leq$  5.5 V, NRST/NIRQ Voltage = 10 k $\Omega$  to VDD, NRST/NIRQ load = 10 pF, and over the operating free-air temperature range of – 40°C to 125°C, unless otherwise noted. Typical values are at T<sub>A</sub> = 25°C, typical conditions at VDD= 3.3 V.

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
TSD Hysterisis	Thermal Shutdown Hysteresis			25		°C
I2C Electrical	I2C Electrical Specifications					
Св	Capacitive load for SDA and SCL				400	pF
SDA, SCL	Low Threshold, OTP = 3.3 V				0.84	V
SDA, SCL	Low Threshold, OTP = 3.3 V		2.31			V
SDA	Output Low with 3 mA sink current				0.2	V

## 7.6 Timing Requirements

At 2.2 V  $\leq$  VDD  $\leq$  5.5 V, NIRQ/NRST Voltage = 10 k $\Omega$  to VDD, NIRQ/NRST load = 10 pF, and over the operating free-air temperature range of – 40°C to 125°C, unless otherwise noted. Typical values are at T<sub>A</sub> = 25°C, typical conditions at VDD = 3.3 V.

			MIN	NOM	MAX	UNIT
Common	parameters					
t <sub>D_ENx</sub>	ENx toggle delay from start of time slot	From start of time slot			10	μs
t <sub>D_ENx,y</sub>	Delay between 2 subsequent EN in same time slot				1	μs
t <sub>NRST_EN</sub>	ENx delay from NRST in Emergency Shutdown	Sequence 2	200			ns
t <sub>D_NRST</sub>	NRST assertion latency from falling edge of ACT pin below VIL or falling edge of VDD pin below VDD <sub>min</sub>				25	μs
t <sub>D_NIRQ</sub>	Fault detection to NIRQ assertion latency				25	μs
t <sub>No_BIST</sub>	POR to ready without BIST	including OTP load with ECC			2.5	ms
I2C Timing	Characteristics				'	
f <sub>SCL</sub>	Serial clock frequency (1)	Standard mode			100	kHz
f <sub>SCL</sub>	Serial clock frequency (1)	Fast mode			400	kHz
f <sub>SCL</sub>	Serial clock frequency (1)	Fast mode +			1	MHz
t <sub>LOW</sub>	SCL low time (1)	Standard mode	4.7			μs
t <sub>LOW</sub>	SCL low time <sup>(1)</sup>	Fast mode	1.3			μs
t <sub>LOW</sub>	SCL low time <sup>(1)</sup>	Fast mode +	0.5			μs
t <sub>HIGH</sub>	SCL high time <sup>(1)</sup>	Standard mode	4			μs
t <sub>HIGH</sub>	SCL high time (1)	Fast Mode	1			μs
t <sub>HIGH</sub>	SCL high time (1)	Fast mode +	0.26			μs
t <sub>SU_DAT</sub>	Data setup time (1)	Standard mode	250			ns
t <sub>SU_DAT</sub>	Data setup time <sup>(1)</sup>	Fast mode	100			ns
t <sub>SU_DAT</sub>	Data setup time (1)	Fast mode +	50			ns
t <sub>HD_DAT</sub>	Data hold time (1)	Standard mode	10		3450	ns
t <sub>HD_DAT</sub>	Data hold time (1)	Fast mode	10		900	ns
t <sub>HD_DAT</sub>	Data hold time (1)	Fast mode +	10			ns
t <sub>SU_STA</sub>	Setup time for a Start or Repeated Start condition (1)	Standard mode	4.7			μs
t <sub>SU_STA</sub>	Setup time for a Start or Repeated Start condition (1)	Fast mode	0.6			μs
t <sub>SU_STA</sub>	Setup time for a Start or Repeated Start condition (1)	Fast mode +	0.26			μs
t <sub>HD_STA</sub>	Hold time for a Start or Repeated Start condition (1)	Standard mode	4			μs
t <sub>HD_STA</sub>	Hold time for a Start or Repeated Start condition (1)	Fast mode	0.6	,		μs

English Data Sheet: SNVSCG1



# 7.6 Timing Requirements (continued)

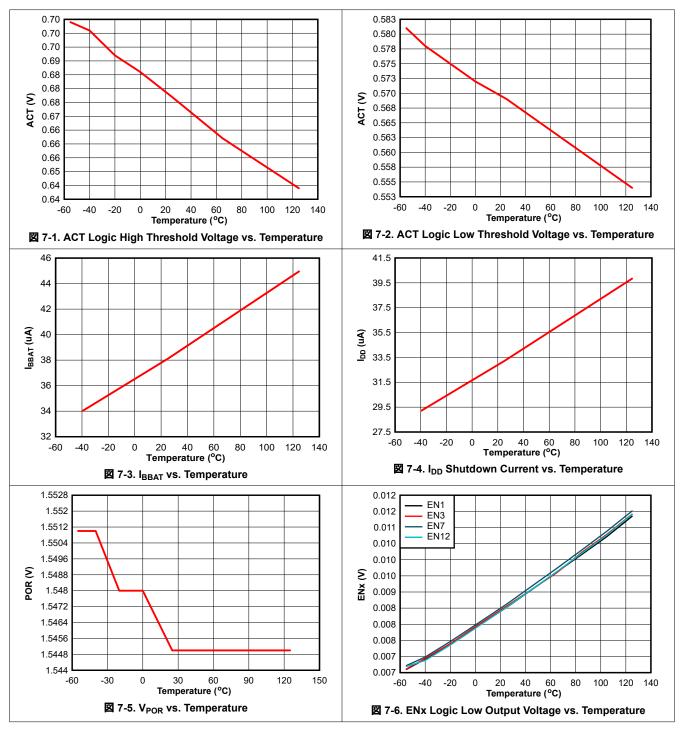
At 2.2 V  $\leq$  VDD  $\leq$  5.5 V, NIRQ/NRST Voltage = 10 k $\Omega$  to VDD, NIRQ/NRST load = 10 pF, and over the operating free-air temperature range of – 40°C to 125°C, unless otherwise noted. Typical values are at  $T_A$  = 25°C, typical conditions at VDD = 3.3 V.

			MIN	NOM	MAX	UNIT
t <sub>HD_STA</sub>	Hold time for a Start or Repeated Start condition (1)	Fast mode +	0.26			μs
t <sub>BUF</sub>	Bus free time between a STOP and START condition (1)	Standard mode	4.7			μs
t <sub>BUF</sub>	Bus free time between a STOP and START condition (1)	Fast mode	1.3			μs
t <sub>BUF</sub>	Bus free time between a STOP and START condition (1)	Fast mode +	0.5			μs
t <sub>su_sto</sub>	Setup time for a Stop condition (1)	Standard mode	4			μs
t <sub>su_sto</sub>	Setup time for a Stop condition (1)	Fast mode	0.6			μs
t <sub>su_sto</sub>	Setup time for a Stop condition (1)	Fast mode +	0.26			μs
t <sub>rDA</sub>	Rise time of SDA signal (1)	Standard mode			1000	
t <sub>rDA</sub>	Rise time of SDA signal (1)	Fast mode	20		300	ns
t <sub>rDA</sub>	Rise time of SDA signal (1)	Fast mode +			120	ns
t <sub>fDA</sub>	Fall time of SDA signal <sup>(1)</sup>	Standard mode			300	ns
t <sub>fDA</sub>	Fall time of SDA signal <sup>(1)</sup>	Fast mode	1.4		300	ns
t <sub>fDA</sub>	Fall time of SDA signal <sup>(1)</sup>	Fast mode +	6.5		120	ns
t <sub>rCL</sub>	Rise time of SCL signal (1)	Standard mode			1000	ns
t <sub>rCL</sub>	Rise time of SCL signal (1)	Fast mode	20		300	ns
t <sub>rCL</sub>	Rise time of SCL signal (1)	Fast mode +			120	ns
t <sub>fCL</sub>	Fall time of SCL signal <sup>(1)</sup>	Standard mode			300	ns
t <sub>fCL</sub>	Fall time of SCL signal <sup>(1)</sup>	Fast mode	6.5		300	ns
t <sub>fCL</sub>	Fall time of SCL signal <sup>(1)</sup>	Fast mode +	6.5	,	120	ns
t <sub>SP</sub>	Pulse width of SCL and SDA spikes that are suppressed (1)	Standard mode, Fast mode and Fast mode +			50	ns

(1) Guaranteed by design

# 7.7 Typical Characteristics

At  $T_A$  = 25°C,  $V_{DD}$  = 3.3 V, and  $R_{PU}$  = 10 k $\Omega$ , unless otherwise noted.



English Data Sheet: SNVSCG1



# 8 Detailed Description

#### 8.1 Overview

When designing a complicated system with many power rails, you must not overlook how and when rails are turned on. Sequencing sub-systems can be implemented in various ways. Theoretically a system can chain PGOOD signals from Power IC's to the enable subsequent power rails. This is not recommended, however, as there's no easy way to disable the system once it's been turned on.

TPS38700S-Q1 operates similarly to a PGOOD based protocol, but is able to bypass the powering down dilemma by having a handshake based PGOOD protocol with SYNC for both sequencing up and down. TPS38700S-Q1 waits for the SYNC signal from the TPS389006-Q1 Device indicating the voltage met a UV PGOOD or OFF threshold before firing the next signal.

Another way a system can also implement sequencing is with a blind firing approach. The blind firing approach turns on subsequent rails after a small time delay regardless of whether or not the rails power on. This can be useful in systems where power rails don't have any critical voltage dependencies, but the order of how the rails are turned on and off is important. You can implement a Non-Monitored sequencing approach like this with the **N** OTP variant of TPS 38700S-Q1.

TPS38700S-Q1 is a versatile part that can be configured for multiple ways. The part can be ordered as a pure sequencer, pure GPO expander, or combination sequencer & GPOs. Sequencing outputs can be assigned to ACT pin. These sequencing outputs can be factory configured for default values and subsequently changed via  $I^2C$  on power-up before sending ACT pin high.

The TPS38700S-Q1 is capable of various I<sup>2</sup>C logic levels. A full featured Graphical User Interface (GUI) is available for download in the product folder. Contact a Texas Instruments representative for custom configured part queries.

The TPS38700S-Q1 is AEC-Q100 qualified for automotive applications and has been characterized from -40°C to +125°C.

# 8.2 Functional Block Diagram

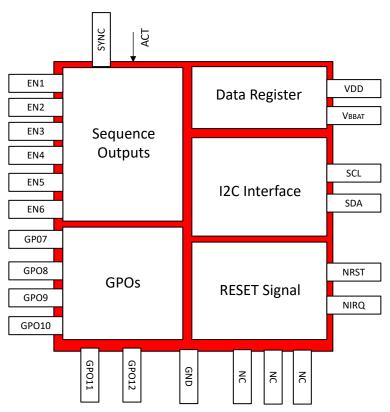


図 8-1. TPS38700S-Q1 Block Diagram



# **8.3 Feature Description**

## 8.3.1 Device State Diagram

The TPS38700S-Q1 state diagrams shown in ⊠ 8-2 show the flow of operation.

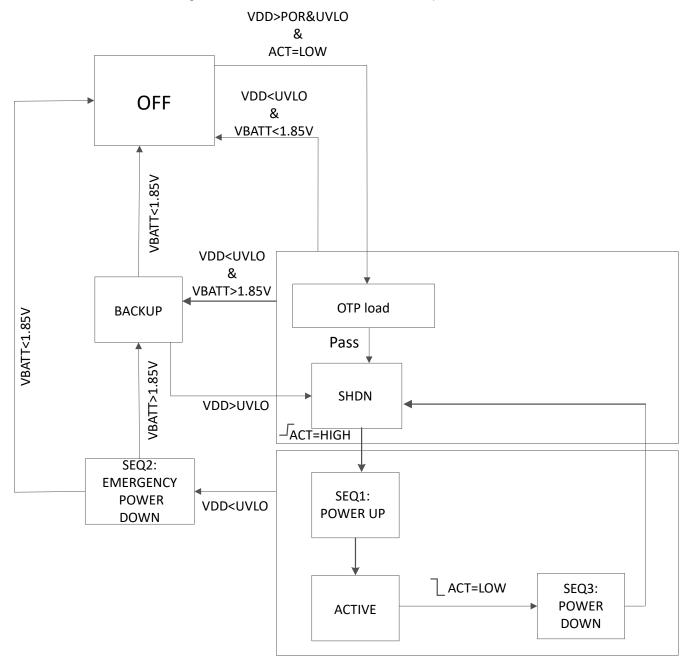


図 8-2. TPS38700S-Q1 State Diagram

English Data Sheet: SNVSCG1

#### 8.3.2 Sync Functionality

A typical implementation of the sync functionality of the TPS38700S-Q1 is shown in 🗵 8-3. TPS38700S-Q1 and TPS389006-Q1 can be used together by tying SYNC pins together in order to ensure that sequential voltage rails are dependent on earlier voltage rails successfully powering up or powering down.

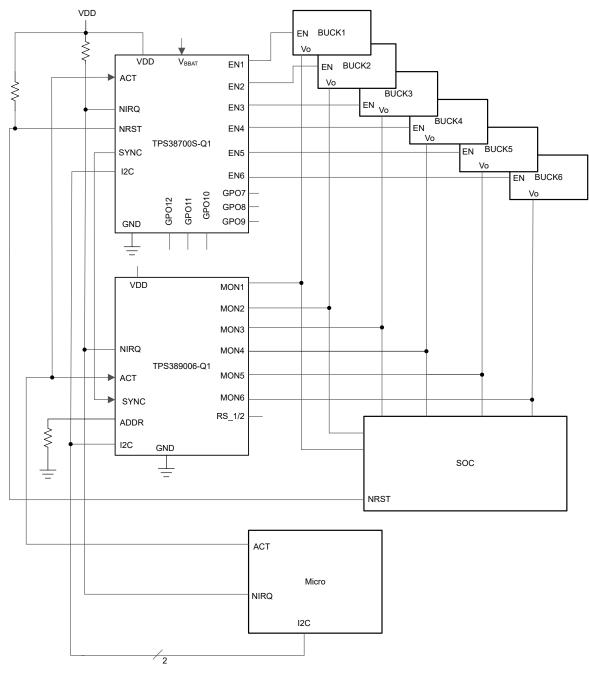


図 8-3. TPS38700S Voltage Sequencer Design Block Diagram

SYNC is an active low input on the TPS38700S-Q1 which causes EN pins to toggle on when sequencing up or off when sequencing down. TPS389006-Q1 will send an active low signal when the desired voltage threshold is monitored. For more information on how sequence logging works and how TPS389006-Q1 tags power rails with SYNC check out the TPS389006-Q1 data sheet.



#### 8.3.3 Transitioning Sequences

The sequences of the device are described in セクション 8.3.3.1 through セクション 8.3.3.3 with timing diagrams showing the main signals involved in each sequence.

#### 8.3.3.1 Power Up

When ACT is driven high, the first EN signal is turned on by TPS38700S-Q1. Then, the MON voltage rises and triggers TPS389006-Q1 to send the first SYNC signal which causes TPS38700S-Q1 to turn on the second EN voltage. This process repeats until all Enable voltages turn on. After the final EN signal is turned on, NRST deactivates after the RST\_DLY time. A successful power up sequence is shown in  $\boxtimes$  8-4 using the circuit shown in  $\boxtimes$  9-1. Note that the TPS389006-Q1 defaults to using UV thresholds for sending the SYNC pulse when sequencing up.

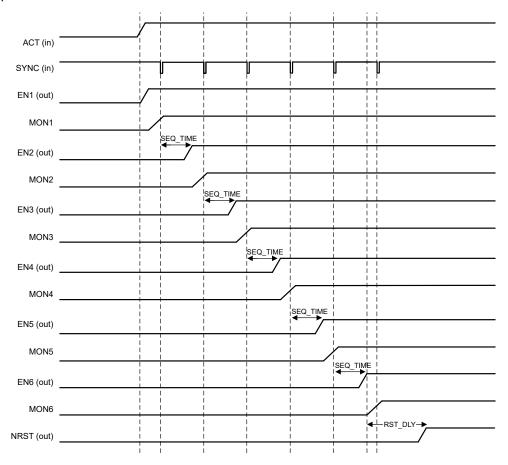


図 8-4. TPS38700S Power Up with SYNC

#### 8.3.3.2 Power Down

A similar sequence of events happens when ACT is driven low. Immediately the first EN signal in the down sequence is driven low. This triggers TPS389006-Q1 by having the MON voltage drop below a threshold and send a SYNC signal. The SYNC signal causes TPS38700S-Q1 to turn off the second EN signal. This process also repeats until all voltages have been turned off. By default SYNC voltage thresholds for TPS389006-Q1 are based on the OFF voltage. The voltage thresholds can be changed to UV voltage thresholds for both sequencing up and down. A successful power down sequence is shown in  $\boxtimes$  8-5 using the circuit shown in  $\boxtimes$  9-1. Note that the TPS389006-Q1 defaults to using OFF voltage threshold (MONx<140mV) for sending the SYNC pulse when sequencing down.

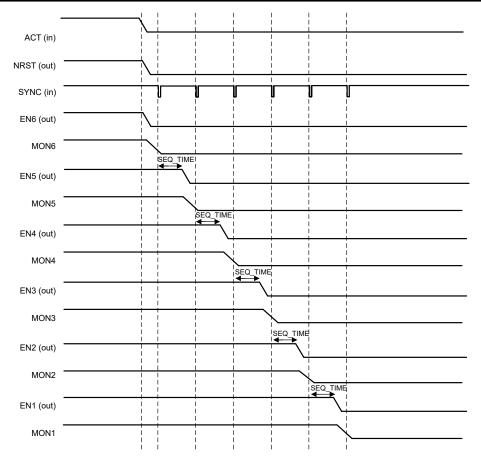


図 8-5. TPS38700S Power Down with SYNC

Note that TPS38700S-Q1 must finish sequencing (either up or down) before starting a new sequence.

## 8.3.3.3 Emergency Power Down

In case of emergency power down (VDD drops below UVLO), a best effort approach is taken to assert NRST before pulling ENx and NIRQ down.

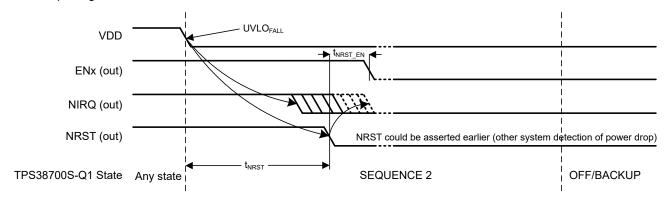


図 8-6. Emergency Power Down

#### 8.3.4 BACKUP State

In the BACKUP state only the battery is supplying power to the device, however the device must have gone through a VDD supplied state (and loaded configuration data) in order to enter this state. If no VDD supplied



state has occurred, then the TPS38700S-Q1 stays in the "OFF or Battery Installed" state, from which it will exit only with a valid VDD supply. I<sup>2</sup>C commincation with TPS38700S-Q1 is possible when in this state.

When in BACKUP state, the TPS38700S-Q1 pins are in the following state:

- ENx = Low (de-asserted)
- NRST = Low (asserted)
- ACT input is ignored.

Upon exiting from the BACKUP state, the last configuration is active and the device enters the SHDN state.

#### 8.3.5 Thermal Shutdown (TSD) State

In the TSD state TPS38700S-Q1 reduces functionality to only support I<sup>2</sup>C commincation. Upon exiting from the TSD state, the last configuration is active and the device enters the SHDN state.

When in BACKUP state, the TPS38700S-Q1 pins are in the following state:

- ENx = Low (de-asserted)
- NRST = Low (asserted)
- ACT input is ignored.

Note that the F\_TSD bit in  $\frac{1}{2}$  8-4 will be set high. The F\_TSD bit will stay high even if TPS38700S-Q1 leaves the TSD state, but can be manually cleared.

#### 8.3.6 I<sup>2</sup>C

TPS38700S-Q1 follows the I<sup>2</sup>C protocol (up to 1MHz) to manage communication with host devices such as a MCU or System on Chip (SoC). I<sup>2</sup>C is a two wire communication protocol implmented using two signals, clock (SCL) and data (SDA). The host device is the primary controller of communication. TPS38700S-Q1 responds over the data line during read or write operations as defined by I<sup>2</sup>C protocol. Both SCL and SDA signals are open drain topology and can be used in a wired-OR configuration with other devices to share the communication bus. Both SCL and SDA pins need an external pull up resistor to supply voltage (10 k $\Omega$  recommended).

⊠ 8-7 shows the timing relationship between SCL and SDA lines to transfer 1 byte of data. SCL line is always controlled by host. To transfer 1 byte data, host needs to send 9 clocks on SCL. 8 clocks for data and 1 clock for ACK or NACK. SDA line is controlled by either the host or TPS38700S-Q1 based on the read or write operation. 

☑ 8-8 and ☑ 8-9 highlight the communication protocol flow and which device controls SDA line at various instances during active communication.

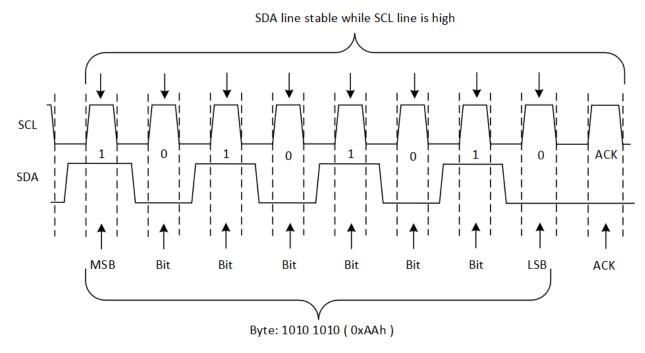


図 8-7. SCL to SDA Timing for 1 Byte Data Transfer

Controller Controls SDA Line

Target Controls SDA Line

# Write to One Register in a Device

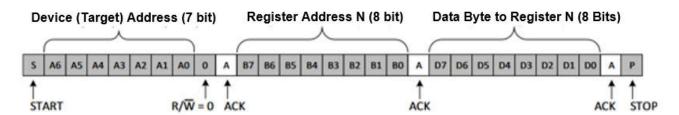


図 8-8. I<sup>2</sup>C Write Protocol

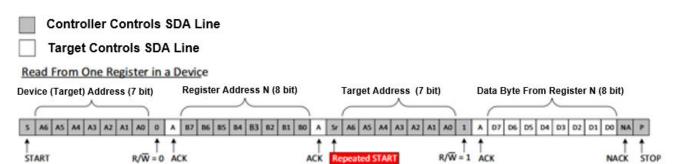


図 8-9. I<sup>2</sup>C Read Protocol

Before initiating communication over  $I^2C$  protocol, host needs to confirm the  $I^2C$  bus is available for communication. Monitor the SCL and SDA lines, if any line is pulled low, the  $I^2C$  bus is occupied. Host needs to wait until the bus is available for communication. Once the bus is available for communication, the host can initiate read or write operation by issuing a START condition. Once the  $I^2C$  communication is complete, release the bus by issuing STOP command.  $\boxtimes$  8-10 shows how to implement START and STOP condition.

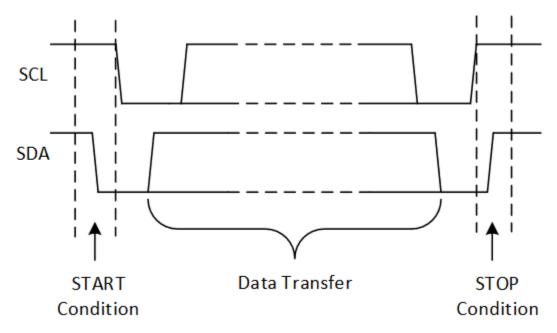


図 8-10. I<sup>2</sup>C START and STOP Condition

# 8.3.6.1 I<sup>2</sup>C

Refer to  $\frac{1}{2}$ C register map overview. Note that "PSEQ" refers to TPS38700S-Q1 and is used enhance table readability.

表 8-1. I<sup>2</sup>C Register Categories and Associated Details

		The regions	Categories and Ass			140145 0550
TYPE	BITS	DESCRIPTION	RANGE / FUNCTION OR STATUS	WHO TOGGLES THEM?	WHO ELSE CAN WRITE TO THEM?	WHAT GETS AFFECTED DUE TO THIS BIT?
	VENDORID[7:0]	TI defined	TI defined	OTP option	None	None
OTP bits R	MODEL_REV[7:0]	TI defined	TI defined	OTP option	None	None
	TARGET_ID[7:0]	TI defined	TI defined	OTP option	None	I <sup>2</sup> C
	F_INTERR	Internal fault	No internal fault / Internal fault detected	Interrupt	Any of the interrupts generated; Can be cleared by writing 1	NIRQ
	EM_PD (1)	Emergency Power down	No emergency PD / shutdown caused by emergency PD	PSEQ	PSEQ; SOC	NRST; NIRQ
Interrupt info bits RW1C	F_EN	Enable output pin fault	No faults detected / fault detected	EN readback- PSEQ	PSEQ; SOC	NIRQ; NRST
	F_NRSTIRQ	Reset or Interrupt pin fault	No faults detected / fault detected	Reset readback- PSEQ	PSEQ; SOC	NIRQ
	F_LDO	LDO fault	No faults detected / fault detected	BIST	BIST; SOC	NIRQ; NRST
	F_TSD	Thermal shutdown fault	No faults detected / fault detected	TSD	TSD; SOC	NIRQ; NRST
	F_RT_CRC	Runtime CRC register fault	No faults detected / fault detected	CRC	soc	NIRQ
	ST_NIRQ	Current state of NIRQ output	NIRQ asserted / not asserted	Interrupt	None	None
	ST_NRST	Current state of NRST output	NRST asserted / not asserted	Interrupt; NRSTstate change	None	None
Status bits	ST_ACTSHDN	Current state of ACT input	ACT pin driven Low or High	PSEQ	None	None
R	ST_PSEQ[1:0]	Current state of PSEQ	SHDNx, Power Up, Power Down, invalid, Active	PSEQ	None	None
	STDR1	Current drive state of GPO12 to GPO9	Sequencer is driving EN Low or High	PSEQ	None	None
	STDR2	Current drive state of GPO7,8 to EN1	Sequencer is driving EN Low or High	PSEQ	None	None
	FORCE_INT	Force NIRQ low	NIRQ contolled by faults / register	SOC	soc	NRST
CONTROL R/W	FORCE_ACT	Force PSEQ Active state		PSEQ	SOC can clear it; but not set it	PSEQ
	RST_DLY[3:0]	Reset Delay	0.1 ms to 128 ms	SOC	None	PSEQ

表 8-1. I<sup>2</sup>C Register Categories and Associated Details (continued)

TYPE	вітѕ	DESCRIPTION	RANGE / FUNCTION OR STATUS	WHO TOGGLES THEM?	WHO ELSE CAN WRITE TO THEM?	WHAT GETS AFFECTED DUE TO THIS BIT?
	USLOT[3:0]	Power Up time slots	125 µs / 2.5 s	SOC	None	PSEQ
	DSLOT[3:0]	Power Down time slots	125 µs / 2.5 s	soc	None	PSEQ
PSEQ	SSTEP	Slot step multiplier	250 µs / 1000 µs	SOC	None	PSEQ
	PU[3:0][12:1]	Power Up Sequence	ENx not mapped / ENx mapped	soc	None	PSEQ
	PD[3:0][12:1]	Power Down Sequence	ENx not mapped / ENx mapped	soc	None	PSEQ
	WRK	Work set register lock	0 / 1	SOC only 1	None	Write function to those register groups
	SEQS	SEQS set register lock	0 / 1	SOC only 1	None	Write function to those register groups
PROT	SEQP	SEQP set register lock	0 / 1	SOC only 1	None	Write function to those register groups
	SEQC	SEQC set register lock	0 / 1	SOC only 1	None	Write function to those register groups
	CTL	CTL set register lock	0 / 1	SOC only 1	None	Write function to those reg groups

<sup>(1)</sup> Presence of fault reporting functionality dependent on part configuration.

# 8.4 Register Map Table

# 表 8-2. Register Map Table

RSVD = Reserved

ADDR	NAME	R/W	MSB	6	5	4	3	2	1	LSB	DEFAULT	GROUP
0x00 - 0x	0F: Vendor info an	nd vendor i	usage registers	<b>3</b>								ı
0x00	Model Rev	R		Dev	ice Model (Bits	3-7)		Ve	endor ID (Bits 0	-2)		
0x01	Revision	R	Silicor	n_Rev			ОТР	_Rev				
0x02 0x0F	RSVD				Ven	dor defined or	other IC informa	ation				
0x10 - 0x	1F: Interrupts and	Status reg	jisters							•		-
0x10	INT_SRC1	RW1C	F_INTERNAL	EM_PD	RSVD	RSVD	RSVD	F_EN	RSVD	F_NRSTIRQ	0x00	
0x11	INT_SRC2	RW1C	F_VENDOR	RSVD	F_RT_CRC	RSVD	F_LDO	F_TSD	RSVD	RSVD	0x00	
0x12	INT_VENDOR	RW1C			V	endor specific	internal fault fla	gs			0x00	
0x13	CTL_STAT	R	RSVD	ST_VBBAT	ST_NIRQ	ST_NRST	RSVD	ST_ACTSHD N	ST_PS	EQ[1:0]	0x00	
0x14	EN_STDR1	R		RS	VD		STDR_GPO1	STDR_GPO1 1	STDR_GPO1 0	STDR_GPO9	0x00	
0x15	EN_STDR2	R	STDR_GPO8	STDR_GP07	STDR_EN6	STDR_EN5	STDR_EN4	STDR_EN3	STDR_EN2	STDR_EN1	0x00	
0x16	EN_STRD1	R		RS	VD		STRD_GPO1	STRD_GPO1 1	STRD_GPO1 0	STRD_GPO9	0x00	
0x17	表 8-10	R	STRD_GPO8	STRD_GP07	STRD_EN6	STRD_EN5	STRD_EN4	STRD_EN3	STRD_EN2	STRD_EN1	0x00	
0x18 0x19	RSVD					RS	SVD					
0x1A	表 8-11	R	RSVD	RSVD	RSVD	RSVD	ACTSHDN	RSVD	RSVD	RSVD	0x00	
0x1B 0x1F	RSVD					RS	SVD					
0x20 - 0x	2F: Configuration	Registers										
0x20 0x26	RSVD	R		RSVD					NVM			
0x27	RSVD	R/W	RSVD				NVM	CTL				
0x28	CTL_1	R/W	RSVD			FORCE_INT	FORCE_ACT	RSVD	RSVD	NVM	WRK	
0x29	表 8-14	R/W		RST_D	LY[3:0]		RS	SVD	RSVD	RSVD	NVM	CTL
0x2B	IEN_VENDOR	R/W			Ve	ndor specifc in	ternal fault enat	oles	I		NVM	CTL
0x2C 0x2F	RSVD					RS	SVD					

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23



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# 表 8-2. Register Map Table (continued)

## RSVD = Reserved

24

ADDR	NAME	R/W	MSB	6	5	4	3	2	1	LSB	DEFAULT	GROUP
0x30 - 0x3	88: Sequencing R	egisters		l.			•	•			•	1
0x30	SEQ_CFG	R/W				RSVD				SSTEP	NVM	SEQC
0x31	SEQ_USLOT	R/W				TIM	<b>Ξ</b> [7:0]			•	NVM	SEQC
0x32	SEQ_DSLOT	R/W				TIM	Ξ[7:0]				NVM	SEQC
0x33	PWR_EN1	R/W		PU	[3:0]			PD	[3:0]		NVM	SEQP
0x34	PWR_EN2	R/W		PU	[3:0]			PD	[3:0]		NVM	SEQP
0x35	PWR_EN3	R/W		PU	[3:0]			PD	NVM	SEQP		
0x36	PWR_EN4	R/W		PU	[3:0]		PD[3:0]				NVM	SEQP
0x37	PWR_EN5	R/W		PU	[3:0]		PD[3:0]				NVM	SEQP
0x38	PWR_EN6	R/W		PU	[3:0]		PD[3:0]				NVM	SEQP
0xF0 - 0xF	F: Protection reg	isters										
0xF0	PROT1	R/W	RSVD	WRK	SEQS	SEQP	SEQC	WDT	RSVD	CTL	0x00	
0xF1	PROT2	R/W	RSVD	WRK	SEQS	SEQP	SEQC	WDT	RSVD	CTL	0x00	
0xF2 0xF8	RSVD			RSVD								
0xF9	I2CADDR	R	RSVD	RSVD AE				DDR_I2C_NVM[6:0]				
0xFA 0xFF	RSVD			1		RS	SVD					

#### 8.4.1 Register Descriptions

## 表 8-3. INT\_SRC1

Address: 0x10

Description: Interrupt Source register. If F\_INTERNAL, then INT\_SRC2 register provides further information.

POR Value: 0x00

Access: Read and write 1 to clear. Writing 0 has no effect; writing 1 to a bit which is already at 0 has no effect.

Back to Register Map Table.

BIT	NAME	DESCRIPTION
7	F_INTERNAL	Internal Fault (ORed value of all bits in INT_SRC2): 0 = No internal fault detected 1 = Internal fault detected. Further detail flagged in INT_SRC2. This bit is cleared by clearing the bits in INT_SRC2.
6	EM_PD	Emergency Power Down:  0 = No emergency power-down event  1 = Shutdown caused by emergency power-down (Sequence 2).  Write-1-to-clear will clear the bit. The bit will be set again on next emergency power-down.
3	RSVD	RSVD
2	F_EN	Enable Output Pin Fault:  0 = No short to supply or ground detected. 1 = Short to supply or ground detected.  Write-1-to-clear will clear the bit only if the fault condition is also removed.
1	RSVD	RSVD
0	F_NRSTIRQ	Reset or Interrupt Pin Fault:  0 = No fault detected on NRST or NIRQ.  1 = Low resistance path to supply detected on either NRST or NIRQ.  Write-1-to-clear will clear the bit only if the fault condition is also removed.

INT\_SRC1 represents the reason that NIRQ was asserted. When the host processor receives NIRQ, it may read this register to quickly determine the source of the interrupt. If this register is clear, then TPS38700S-Q1 did not assert NIRQ.

## 表 8-4. INT\_SRC2

Address: 0x11

Description: Interrupt Source register for internal errors.

POR Value: 0x00

Access: Read and write 1 to clear. Writing 0 has no effect; writing 1 to a bit which is already at 0 has no effect.

Back to Register Map Table.

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BIT	NAME	DESCRIPTION		
7	F_VENDOR	Vendor specific internal fault. Details reported in INT_VENDOR. This bit represents the ORed value of all bits in INT_VENDOR.  0 = No fault reported in INT_VENDOR 1 = Fault reported in INT_VENDOR  This bit is cleared by clearing the bits in INT_VENDOR.		
6	RSVD	Reserved		

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## 表 8-4. INT\_SRC2 (continued)

Address: 0x11

Description: Interrupt Source register for internal errors.

POR Value: 0x00

Access: Read and write 1 to clear. Writing 0 has no effect; writing 1 to a bit which is already at 0 has no effect.

#### Back to Register Map Table.

BIT	NAME	DESCRIPTION
5	F_RT_CRC	Runtime register CRC Fault:  0 = No fault detected.  1 = Register CRC fault detected.  Write-1-to-clear will clear the bit. The bit will be set again during next register CRC check if a fault is detected.
3	F_LDO	LDO Fault:  0 = No LDO fault detected. 1 = LDO fault detected.  If internal LDO is used, this flag is to indicate fault.  If internal LDO is not used, this flag must be reserved.  Write-1-to-clear will clear the bit only if the fault condition is also removed.
2	F_TSD	Thermal Shutdown:  0 = No thermal shutdown.  1 = Thermal shutdown occurred since last read.  Write-1-to-clear will clear the bit only if the fault condition is also removed.

# 表 8-5. INT\_VENDOR

Address: 0x12

Description: Vendor Specific Internal Interrupt Status register.

POR Value: 0x00

Access: Read and write 1 to clear. Writing 0 has no effect; writing 1 to a bit which is already at 0 has no effect.

## Back to Register Map Table.

ВІТ	NAME	DESCRIPTION
7:0	FAULTS[7:0]	Vendor specific internal faults flags.

## 表 8-6. CTL\_STAT

Address: 0x13

Description: TPS38700S-Q1 Status register for control pins and internal state.

POR Value: 0x00 Access: Read only.

#### Back to Register Map Table.

BIT	NAME	DESCRIPTION
7:6	RSVD	Reserved
5	ST_NIRQ	Current state of NIRQ Output:  0 = NIRQ pin asserted low by TPS38700S-Q1.  1 = NIRQ pin not asserted low by TPS38700S-Q1.

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# 表 8-6. CTL\_STAT (continued)

Address: 0x13

Description: TPS38700S-Q1 Status register for control pins and internal state.

POR Value: 0x00 Access: Read only.

Back to Register Map Table.

BIT	NAME	DESCRIPTION
4	ST_NRST	Current state of NRST Output:  0 = NRST pin asserted low by TPS38700S-Q1.  1 = NRST pin not asserted low by TPS38700S-Q1.
3	RSVD	RSVD
2	ST_ACTSHDN	Current state of ACT input:  0 = ACT pin driven low (Shutdown) by system. 1 = ACT pin driven high (Active) by system.
1:0	ST_PSEQ[1:0]	00b: SHDNx, Power Up, Power Down 01b: NA 10b: Invalid combination 11b: ACTIVE



## 表 8-7. EN\_STDR1

Address: 0x14

Description: Current drive status of Enable Pins.

POR Value: 0x00 Access: Read only.

#### Back to Register Map Table.

BIT	NAME	DESCRIPTION
7:4	RSVD	Reserved
3:0	STDR_GPO[12:9]	Current drive state of GPO[X]:  0 = TPS38700S-Q1 is driving GPO[X] Low.  1 = TPS38700S-Q1 is driving or allowing to float GPO[X] High.

# 表 8-8. EN\_STDR2

Address: 0x15

Description: Current drive status of Enable Pins.

POR Value: 0x00 Access: Read only.

## Back to Register Map Table.

BIT	NAME	DESCRIPTION
7:0		Current drive state of GPO[X]:  0 = TPS38700S-Q1 is driving GPO[X] Low.  1 = TPS38700S-Q1 is driving or allowing to float GPO[X] High.

## 表 8-9. EN\_STRD1

Address: 0x16

Description: Current read status of Enable Pins.

POR Value: 0x00 Access: Read only.

## Back to Register Map Table.

BIT	NAME	DESCRIPTION
7:4	RSVD	Reserved
3:0		Current read state of GPO[X]: 0 = TPS38700S-Q1 is reading GPO[X] Low. 1 = TPS38700S-Q1 is reading GPO[X] High.

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# 表 8-10. EN\_STRD2

Address: 0x17

Description: Current read status of Enable Pins.

POR Value: 0x00 Access: Read only.

Back to Register Map Table.

BIT	NAME	DESCRIPTION
7:0	STRD_EN[6:1]	Current read state of GPO[X]:
	GPO[8:7]	0 = TPS38700S-Q1 is reading GPO[X] Low.
		1 = TPS38700S-Q1 is reading GPO[X] High.

## 表 8-11. LAST\_RST

Address: 0x1A

Description: Reason of last NRST assertion or shutdown. NRST assertion and shutdown occur in Sequence 2 and Sequence 3.

The register is maintained as long as VDD and/or VBBAT is present. An emergency shutdown triggering Sequence 2 is already recorded in INT\_SRC1.EM\_PD register bit, so it does not need to be stored in this register. The host is expected to read this register as part of the first actions taken upon power ON.

The register is overwritten with new relevant data on next NRST assertion or shutdown.

POR Value: 0x00
Access: Read Only.

Back to Register Map Table.

BIT	NAME	DESCRIPTION
7	RSVD	Reserved
5	RSVD	Reserved
3	ACTSHDN	NRST/Shutdown due to ACT asserted Low (shutdown).  0 = Last NRST/Shutdown assertion was not due to ACT Low.  1 = Last NRST/Shutdown assertion was due to ACT Low.
1	RSVD	Reserved
0	RSVD	Reserved



# 表 8-12. GP\_OUT

Address: 0x25

Description: Set General Purpose Output state for sequencing pins EN[12:9]. GPO is enabled through

AF\_IN\_OUT and EN\_ALT\_F registers.

POR Value: Loaded from NVM.

Access: Read/Write. Read-only if CTL group is protected.

## Back to Register Map Table.

BIT	NAME	DESCRIPTION
7:4	RSVD	Reserved
3	GPO12	GPO12 General Purpose Output. Only used when PWR_EN12 is cleared.  0 = GPO12 pin driven low.  1 = GPO12 pin driven high.
2	GPO11	GPO11 General Purpose Output. Only used when PWR_EN11 is cleared.  0 = GPO11 pin driven low.  1 = GPO11 pin driven high.
1	GPO10	EN10 General Purpose Output. Only used when PWR_EN10 is cleared.  0 = EN10 pin driven low.  1 = EN10 pin driven high.
0	GPO9	GPO9 General Purpose Output. Only used when PWR_EN9 is cleared.  0 = GPO9 pin driven low.  1 = GPO9 pin driven high.



## 表 8-13. CTL\_1

Address: 0x28

Description: Interrupt and State SW control.

POR Value: Loaded from NVM.

Access: Read/Write. Read-only if CTL group is protected.

Back to Register Map Table.

BIT	NAME	DESCRIPTION
7:4	RSVD	Reserved
3	FORCE_INT (1)	Force NIRQ low:  0 = NIRQ pin controlled by INT_SRCx register faults.  1 = NIRQ pin forced low.

(1) FORCE\_INT is used by software for periodic check for internal or external short to VDD on NIRQ pin.

表 8-14. CTL\_2

Address: 0x29

Description: Miscellaneous configuration.

POR Value: Loaded from NVM.

Access: Read/Write. Read-only if CTL group is protected.

Back to Register Map Table.

BIT	NAME	D	ESCRIPTION		
7:4	RST_DLY[3:0]	Power up sequence: NRST rer last ENx assert.	Power up sequence: NRST remains asserted until RST_DLY[3:0] after last ENx assert.		
		0000b = 0.1 ms	1000b = 1 ms		
		0001b = 0.2 ms	1001b = 2 ms		
		0010b = 0.4 ms	1010b = 4 ms		
		0011b = 0.8 ms	1011b = 8 ms		
		0100b = 1.6 ms	1100b = 16 ms		
		0101b = 3.2 ms	1101b = 32 ms		
		0110b = 6.4 ms	1110b = 64 ms		
		0111b = 12.8 ms	1111b = 128 ms		
		Power down sequence: NRST	asserted within t <sub>NRST</sub> of ACT= Low.		
3:2	RSVD	RSVD			

#### 表 8-15. IEN\_VENDOR

Address: 0x2B

Description: Vendor Specific Internal Interrupt Enable register.

POR Value: 0x00 or load from NVM.

Access: Read/Write. Read-only if CTL group is protected.

Back to Register Map Table.

BIT	NAME	DESCRIPTION
7:0	FAULTS[7:0]	Vendor specific internal faults enables.

## 表 8-16. SEQ\_CFG

Address: 0x30

Description: Sequencing configuration.

POR Value: Loaded from NVM.

Access: Read/Write. Read-only if SEQ group is protected.

Back to Register Map Table.

BIT	NAME	DESCRIPTION
7:1	RSVD	Reserved
0		Sequencing time slot step size selection for SEQ_USLOT and SEQ_DSLOT:  0 = Time slot step size t <sub>SSTEP</sub> = 250 µs  1 = Time slot step size t <sub>SSTEP</sub> = 1000 µs

## 表 8-17. SEQ\_USLOT

Address: 0x31

Description: Power Up sequencing time slot configuration.

POR Value: Loaded from NVM.

Access: Read/Write. Read only if SEQ group is protected.

Back to Register Map Table.

BIT	NAME	DESCRIPTION
7:0		Sets time slot between sequencing points on power-up: $t_{USLOT} = SEQ\_USLOT.TIME[7:0] \times t_{SSTEP} + t_{SMIN}$ with $t_{SSTEP}$ set by $SEQ\_CFG.SSTEP$ and $t_{SMIN} = t_{SSTEP}/2$ For the case where $SEQ\_CFG.SSTEP = 0$ , refer to $\frac{1}{2}$ 8-18. For the case where $SEQ\_CFG.SSTEP = 1$ , refer to $\frac{1}{2}$ 8-19.

## 表 8-18. SEQ\_CFG.SSTEP = 0

PARAMETER	SYMBOL	MIN (-6%)	TYPICAL	MAX (+6%)	UNIT
Slot step size	t <sub>SSTEP</sub>	235	250	265	μs
Min slot time (0x00)	t <sub>SMIN</sub>	117.5	125	132.5	μs
Max slot time (0xFF)	t <sub>SMAX</sub>	60042.5	63875	67707.5	μs

#### 表 8-19. SEQ CFG.SSTEP = 1

	,				
PARAMETER	SYMBOL	MIN (-6%)	TYPICAL	MAX (+6%)	UNIT
Slot step size	t <sub>SSTEP</sub>	940	1000	1060	μs
Min slot time (0x00)	t <sub>SMIN</sub>	470	500	530	μs
Max slot time (0xFF)	t <sub>SMAX</sub>	240170	255500	270830	μs



## 表 8-20. SEQ\_DSLOT

Address: 0x32

Description: Power Down sequencing time slot configuration.

POR Value: Loaded from NVM.

Access: Read/Write. Read-only if SEQ group is protected.

Back to Register Map Table.

BIT	NAME	DESCRIPTION
7:0		Sets time slot between sequencing points on power-down: $t_{DSLOT}$ = SEQ_DSLOT.TIME[7:0] × $t_{SSTEP}$ + $t_{SMIN}$ with $t_{SSTEP}$ set by SEQ_CFG.SSTEP and $t_{SMIN}$ = $t_{SSTEP}/2$ See $\frac{1}{8}$ 8-17 for setting details.

## 表 8-21. PWR\_EN[12:1]

Address: PWR\_EN1 (0x33) - PWR\_EN12 (0x3E) (Twelve 8-bit registers).

Description: Power Up/ Down sequence definition by assignment of EN[12:1] to one of fifteen time slots.

Slot=1 is the earliest slot that can be selected and it indicates that the ENx pin will toggle in the first SEQ USLOT.TIME or SEQ DSLOT.TIME after the triggering event.

POR Value: Loaded from NVM.

Access: Read/Write. Read-only if SEQ group is protected.

Back to Register Map Table.

BIT	NAME	DESCRIPTION
7:4	PU[3:0]	Power Up Sequence:  0 = ENx pin not mapped to sequence. ENx maintains previous state, unless entering BACKUP or FAILSAFE state (ENx is pulled low in those states).  1 = ENx pin mapped to first time slot (first up).  15 = ENx pin mapped to last time slot (last up).
3:0	PD[3:0]	Power Down Sequence:  0 = ENx pin not mapped to sequence. ENx maintains previous state, unless entering BACKUP or FAILSAFE state (ENx is pulled low in those states).  1 = ENx pin mapped to first time slot (first down).  15 = ENx pin mapped to last time slot (last down).

#### 表 8-22. PROT1, PROT2

Address: 0xF0, 0xF1

Description: Protection selection registers. In order to write-protect a register group, the host must set the

relevant bit in both registers.

POR Value: 0x00
Access: Read/Write.

For security, these registers need to have POR value=0x00 and become read-only once set until power cycle.

Once set to 1, they cannot be cleared to 0 by the host; a power cycle (VDD=0) is required to write different registers configurations.

#### Back to Register Map Table.

BIT	NAME	DESCRIPTION
7	RSVD	Reserved
6	WRK	0 = Working registers are writable. 1 = Writes to working registers are ignored.
5	RSVD	RSVD
4	SEQP	<ul><li>0 = Power Sequence registers are writable.</li><li>1 = Writes to Power Sequence registers are ignored.</li></ul>
3	SEQC	<ul><li>0 = Sequence slot configuration registers are writable.</li><li>1 = Writes to Sequence slot configuration registers are ignored.</li></ul>
2	RSVD	RSVD
1	RSVD	RSVD
0	CTL	0 = Control registers are writable. 1 = Writes to control registers are ignored.

#### 表 8-23. I2CADDR

Address: 0xF9

Description: I<sup>2</sup>C address.

POR Value: Loaded from NVM.

Access: Read-Only.

## Back to Register Map Table.

BIT	NAME	DESCRIPTION
7	RSVD	Reserved
6:0	ADDR_NVM[6:0]	I <sup>2</sup> C target device address. Set in NVM.

Product Folder Links: TPS38700S-Q1

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# 9 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

## 9.1 Application Information

Modern SOC and FPGA devices typically need multiple power rails to provide power to the different blocks within the respective SOC or FPGA. Accurate voltage level and timing requirements are common and must be met to maintain proper operation of these devices. By utilizing TPS38700S-Q1 along with a multichannel voltage supervisor like the TPS389006-Q1, the power up and power down sequencing requirements as well as the core voltage requirements of the target SOC or FPGA can be met. This design can also assist in meeting the strict timing requirements for an SOC or FPGA.

### 9.2 Typical Application

### 9.2.1 Automotive Multichannel Sequencer and Monitor

A typical application for the TPS38700S-Q1 is shown in 29-1. TPS38700S-Q1 is used to provide the proper voltage sequencing for the target SOC device by providing enable signals to the DC/DC converters shown. These DC/DC converters are used to generate the appropriate voltage rails for the SOC. A mulitchannel voltage monitor like the TPS389006-Q1 is used to monitor the voltage rails as these rails power up and power down to ensure that the correct sequence occurs in both occasions. After a rail successfully powers up, a SYNC pulse will be need to be sent to TPS38700S-Q1 in order to bring up the subsequent power rail. A microcontroller is also used to provide ACT, NIRQ, and I<sup>2</sup>C commands to the TPS38700S-Q1 and the multichannel voltage monitor. The ACT signal from the microcontroller determines when the TPS38700S-Q1 enters into ACTIVE or SHDN states while the NIRQ pin of the TPS38700S-Q1 acts as an interrupt pin that is set when a fault has occurred. For instance, if an external device pulls the NRST pin low, then the TPS38700S-Q1 will trigger an interrupt through the NIRQ pin. I<sup>2</sup>C is used to communicate the type of fault to the host microcontroller. The host microcontroller can clear the fault by writing 1 to the affected register. The power rails for the microcontroller are not shown in 29-1 for simplicity.

Product Folder Links: TPS38700S-Q1



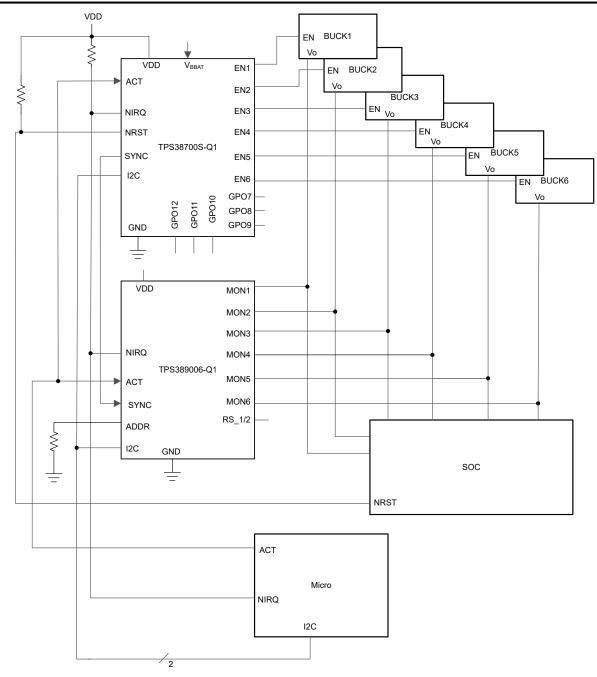


図 9-1. TPS38700S Voltage Sequencer Design Block Diagram

### 9.2.2 Design Requirements

- Eight different voltage rails supplied by DC/DC converters need to be properly sequenced in this design. The sequence order and timing requirements are outlined in 表 9-1.
- Emergency power down functionality is optional.
- Backup battery power supply required. This must be stepped down to a maximum value of 5.5 V in order to comply with the absolute maximum ratings of the V<sub>BBAT</sub> pin.
- All detected failures in sequencing should be reported via an external hardware interrupt signal.
- All detected failures should be logged in internal registers and be accessible to an external processor via I<sup>2</sup>C.

Product Folder Links: TPS38700S-Q1

Ex 9-1. Power op and Power Down Sequence Requirement										
ENABLE CHANNEL	POWER UP SEQUENCE POSITION	POWER DOWN SEQUENCE POSITION	TIME BETWEEN POWER UP SIGNALS (μs)	TIME BETWEEN POWER DOWN SIGNALS (μs)						
EN1	1	4	625	625						
EN2	1	1	625	625						
EN3	2	3	625	625						
EN4	2	3	625	625						
EN5	3	2	625	625						
FN6	4	1	625	625						

表 9-1. Power Up and Power Down Sequence Requirement

#### 9.2.3 Detailed Design Procedure

- TPS38700S-Q1 device comes preprogrammed with the power up, power down sequences shown in 表 9-1.
- NIRQ and NRST pins both require a pull up resistor in the range of 10 kΩ to 100 kΩ.
- SDA and SCL lines require pull up resistors in the range of 10 k $\Omega$ .
- The microcontroller is used to clear fault interrupts reported through the NIRQ interrupt pin and the INT\_SCR1 and INT\_SCR2 registers. The interrupt flags can only be cleared by the host microcntroller with a write-1-to-clear operation; interrupt flags are not automatically cleared if the fault condition is no longer present.

## 9.2.4 Test Implementation

The TPS38700S-Q1 SYNC feature can be demonstrated in a simple test setup with the TPS389006-Q1. For this test, you need the TPS38700Q1EVM-Q1 and the TPS389006Q1EVM-Q1. Replace U1 on the TPS38700Q1EVM with the orderable part TPS38700603SRGERQ1. Replace the U1 on TPS389006Q1EVM with orderable part TPS38900603NRTERQ1. The orderable part TPS38900603NRTERQ1 has initial conditions set such that TPS38700603SRGERQ1 enable voltages meet the UV thresholds to trigger SYNC pulses by default. Connect the system as shown in № 9-2. Connect ACT and VDD to two separate power supplies. Configure the settings over I2C as needed. However, note that power cycling the evaluation modules sets the conditions back to default. If you enable ACT and have done everything correctly, then no LED's should be turned on. If something goes wrong, then either NIRQ on TPS389006-Q1 or NRST on TPS38700S-Q1 will be set low.

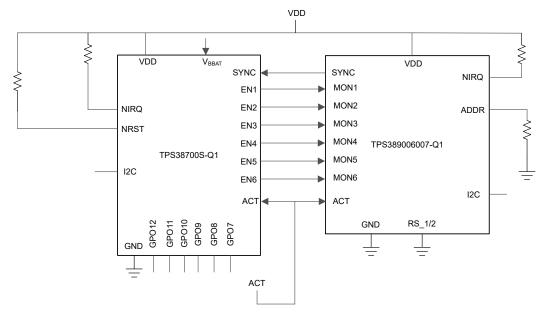


図 9-2. TPS38700S SYNC Test Implementation



Toggling high ACT makes the waveform of the enable voltages look like 29-3 If the waveform does not look that, then to debug check and make sure that everything is connected properly. If the system is connected properly, then verify the I<sup>2</sup>C address values are what you expect the values to be. For example check if the status register of MON1 of TPS389006007-Q1 reads the TPS38700S-Q1 EN voltage output in the Fusion Digital Power Tool.

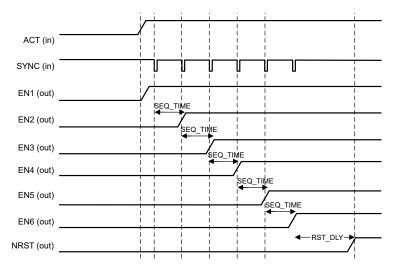


図 9-3. TPS38700S SYNC Sequence Up Test Implementation Waveform

☑ 9-3 shows how the device behaves when ACT is toggled off. Note that there's no delay between when the system detects the ACT falling edge and when NRST and EN6 start sequencing down.

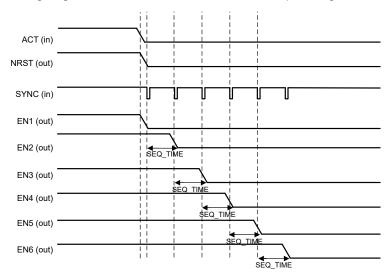
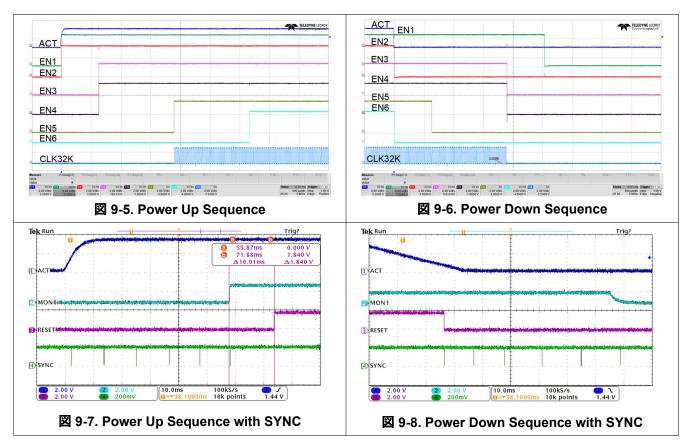


図 9-4. TPS38700S SYNC Sequence Down Test Implementation Waveform

Product Folder Links: TPS38700S-Q1

## 9.2.5 Application Curves





# 10 Power Supply Recommendations

## 10.1 Power Supply Guidelines

This device is designed to operate from an input supply with a voltage range between 2.2 V to 5.5 V. It has a 6 V absolute maximum rating on the VDD pin as well as on the  $V_{BBAT}$  pin. It is good analog practice to place a 0.1- $\mu$ F to 1- $\mu$ F capacitor between the VDD pin and the GND pin depending on the input voltage supply noise. If the voltage supply providing power to VDD is susceptible to any large voltage transients that exceed maximum specifications, additional precautions must be taken.

## 11 Layout

## 11.1 Layout Guidelines

- Place the external components as close to the device as possible. This configuration prevents parasitic errors from occurring.
- Do not use long traces for the VDD supply node. The VDD capacitor, along with parasitic inductance from the supply to the capacitor, can form an LC circuit and create ringing with peak voltages above the maximum VDD voltage.
- Do not use long traces of voltage to the sense pin. Long traces increase parasitic inductance and cause inaccurate monitoring and diagnostics.
- Do not run sensitive analog traces in parallel with digital traces. Avoid crossing digital and analog traces if possible, and only make perpendicular crossings when absolutely necessary.

### 11.2 Layout Example

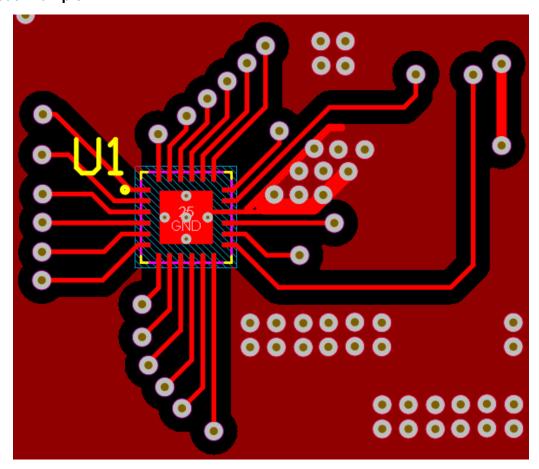


図 11-1. Recommended Layout



## 12 Device and Documentation Support

### 12.1 Device Nomenclature

表 12-1 shows how to decode the function of the device based on the device ordering code, while 図 5-1 shows the sequence configuration based on the device ordering code. See 図 5-1 for more information regarding how to decode the device part number.

### 表 12-1. Device Comparison Table

ORDERING CODE	FUNCTIONS	UNCTIONS EN PINS DEFAULT		TIME SLOT (µsec)	I <sup>2</sup> C ADDR.	RESET DELAY (msec)	I <sup>2</sup> C PULL-UP VOLTAGE (V)
TPS38700603SRGERQ1	Sequencer, GPO	Open-drain	Open-Drain	625	3C	16	3.3

### 12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### 12.3 サポート・リソース

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### 12.6 用語集

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## Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

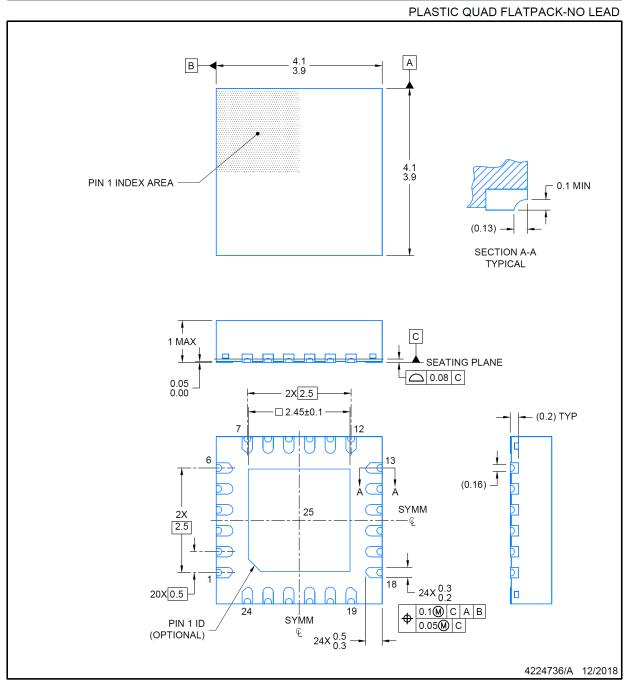
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## **PACKAGE OUTLINE**

# RGE0024N

## VQFN - 1 mm max height



### NOTES:

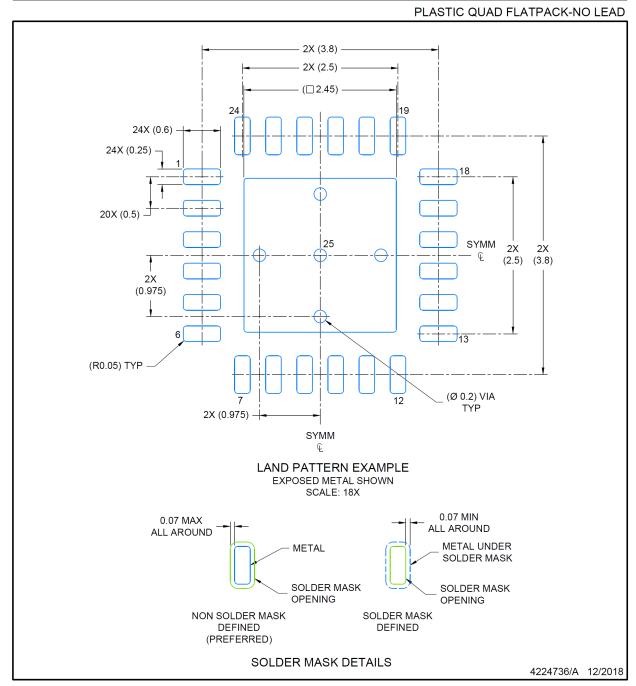
- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.



## **EXAMPLE BOARD LAYOUT**

# RGE0024N

VQFN - 1 mm max height



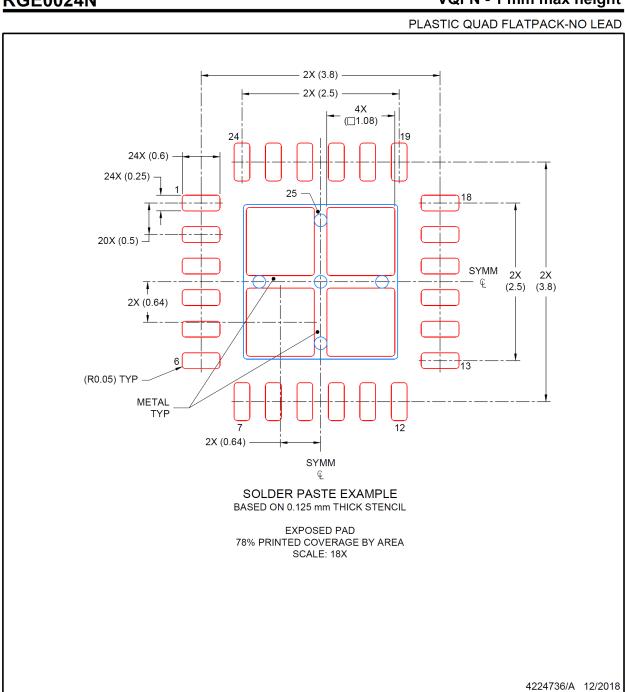
NOTES: (continued)

- This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

## **EXAMPLE STENCIL DESIGN**

# RGE0024N

# VQFN - 1 mm max height



NOTES: (continued)

Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations. www.ti.com 23-May-2025

### PACKAGING INFORMATION

Orderable part number	Status	Material type	Package   Pins	Package qty   Carrier	RoHS	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
						(4)	(5)		
TPS38700603SRGERQ1	Active	Production	VQFN (RGE)   24	3000   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	T387006 03SQA1
TPS38700603SRGERQ1.A	Active	Production	VQFN (RGE)   24	3000   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	T387006 03SQA1

<sup>(1)</sup> Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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<sup>(3)</sup> RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

<sup>(4)</sup> Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

<sup>(5)</sup> MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

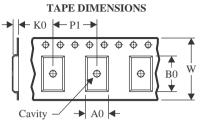
<sup>(6)</sup> Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

# **PACKAGE MATERIALS INFORMATION**

www.ti.com 22-Jul-2023

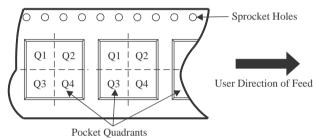
### TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	_	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS38700603SRGERQ1	VQFN	RGE	24	3000	330.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2

# **PACKAGE MATERIALS INFORMATION**

www.ti.com 22-Jul-2023



### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS38700603SRGERQ1	VQFN	RGE	24	3000	367.0	367.0	35.0

PLASTIC QUAD FLATPACK - NO LEAD

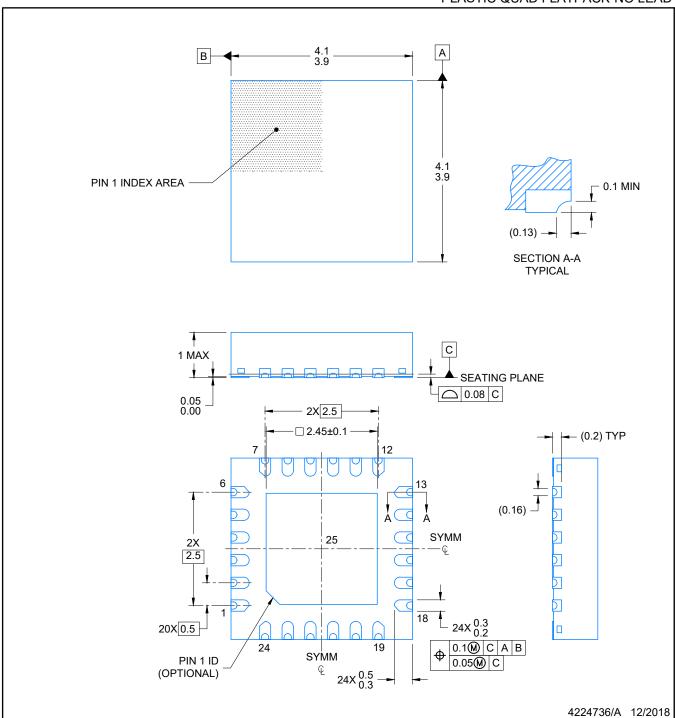


Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

4204104/H



PLASTIC QUAD FLATPACK-NO LEAD

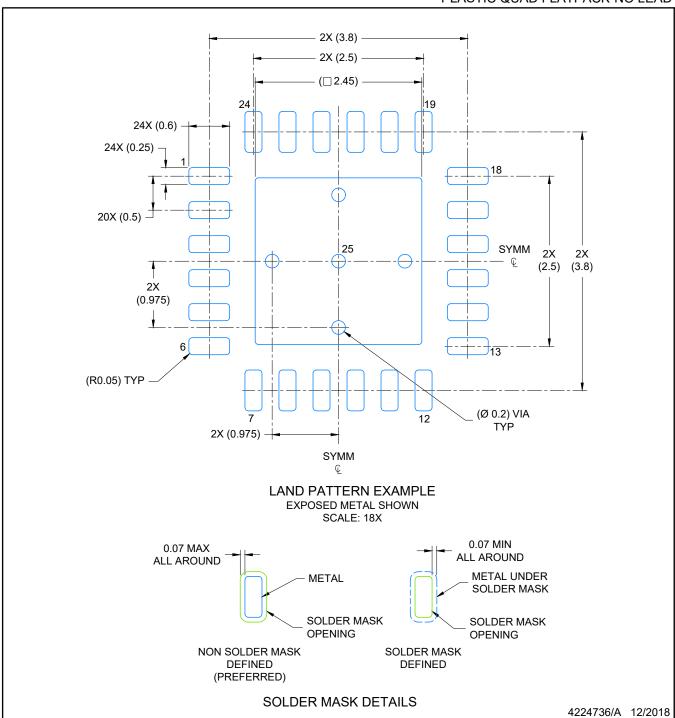


### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
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PLASTIC QUAD FLATPACK-NO LEAD

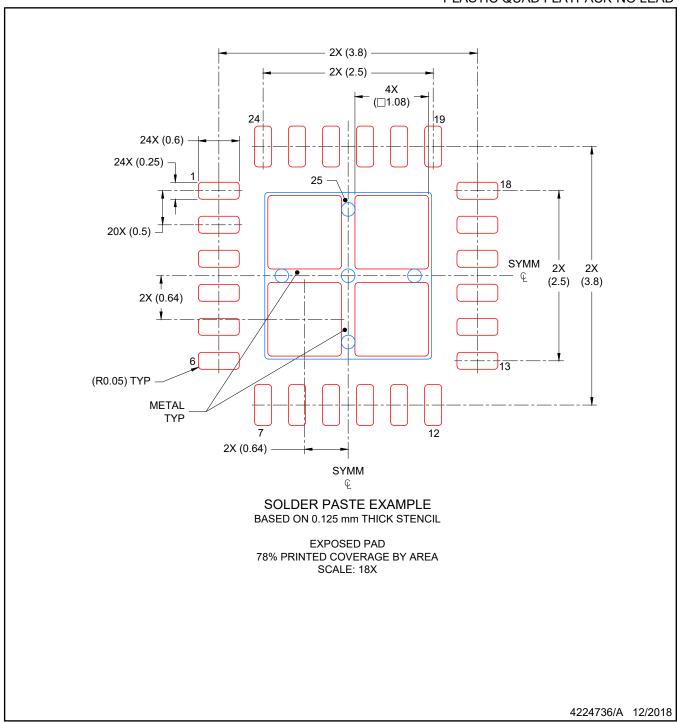


NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



PLASTIC QUAD FLATPACK-NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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